

Amendments to the Specification:

Please replace the Abstract on page 71, with the following rewritten paragraph:

ABSTRACT

In a stacked-layer type photoelectric conversion device, a plurality of photoelectric conversion units (~~3~~; ~~5~~) are stacked on a substrate (~~1~~), each of which includes a one conductivity-type layer (~~31~~; ~~51~~), a photoelectric conversion layer (~~32~~; ~~52~~) of substantially intrinsic semiconductor and an opposite conductivity-type layer (~~33~~; ~~53~~) in this order from a light-incident side. At least one of the opposite conductivity-type layer (~~33~~) in a front photoelectric conversion unit (~~3~~) arranged relatively closer to the light-incident side and the one conductivity-type layer (~~51~~) in a back photoelectric conversion unit (~~5~~) arranged adjacent to the front photoelectric conversion unit (~~3~~) includes a silicon composite layer (~~4~~) at least in a part thereof. The silicon composite layer (~~4~~) has a thickness of more than 20 nm and less than 130 nm and an oxygen concentration of more than 25 atomic % and less than 60 atomic %, and includes silicon-rich phase parts in an amorphous alloy phase of silicon and oxygen.